ABSTRACT AMENDMENTS

Replace the Abstract with:

A semiconductor device has a substrate ~~1~~, a metal wiring ~~3 formed~~ on the substrate ~~1 and covered with the~~ sandwiched by films of a high-melting-point metal ~~2 and 4 immediately above and below~~ and an interlayer insulating film ~~5~~, formed by ~~a~~ plasma CVD ~~method so as to cover~~, covering the metal wiring ~~3~~.